

Dae-Hwan Kang

List of Publications by Year in descending order

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citing authors

#	ARTICLE	IF	CITATIONS
1	One-dimensional heat conduction model for an electrical phase change random access memory device with an 8F2 memory cell ($F=0.15\hat{\epsilon}\%{\hat{I}}{4m}$). Journal of Applied Physics, 2003, 94, 3536-3542.	2.5	143
2	Switching behavior of indium selenide-based phase-change memory cell. IEEE Transactions on Magnetics, 2005, 41, 1034-1036.	2.1	53
3	An experimental investigation on the switching reliability of a phase change memory device with an oxidized TiN electrode. Journal of Applied Physics, 2006, 100, 054506.	2.5	48
4	Characterization of Atomic Layer Deposited $WN_{[sub x]}C_{[sub y]}$ Thin Film as a Diffusion Barrier for Copper Metallization. Journal of the Electrochemical Society, 2004, 151, C272.	2.9	47
5	Atomic-layer-deposited WN_xC_y thin films as diffusion barrier for copper metallization. Applied Physics Letters, 2003, 82, 4486-4488.	3.3	44
6	Lower Voltage Operation of a Phase Change Memory Device with a Highly Resistive TiON Layer. Japanese Journal of Applied Physics, 2004, 43, 5243-5244.	1.5	34
7	Time-resolved analysis of the set process in an electrical phase-change memory device. Applied Physics Letters, 2005, 87, 253504.	3.3	27
8	Understanding on the current-induced crystallization process and faster set write operation thereof in non-volatile phase change memory. Applied Physics Letters, 2012, 100, 063508.	3.3	8